BATOP optoelectronics

SAM™ data sheet SAM-800-4-5ps-x, λ = 800 nm

Laser wavelength	λ = 800 nm
High reflection band	λ = 780 .. 820 nm
Low intensity reflectance	R_0 = 96 %
Absorbance	A_0 =2 %
Modulation depth	ΔR = 1.2 %
Saturation fluence	Φ_{sat} = 60 µJ/cm^2
Relaxation time constant	τ ~ 5 ps
Damage threshold	Φ = 3 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	The SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance